HALOGEN

FREE

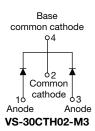


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Vishay Semiconductors

Hyperfast Rectifier, 2 x 15 FRED Pt®





PRIMARY CHARACTERISTICS									
V_{R}	200 V								
V _F at I _F	0.78 V								
t _{rr} typ.	See Recovery table								
T _J max.	175 °C								
I _{F(AV)}	2 x 15 A								
Package	TO-220AB 3L								
Circuit configuration	Common cathode								

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V_{RRM}		200	V						
Average rectified forward current	per diode		T _C = 159 °C	15						
	per device	I _{F(AV)}		30	Α					
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	200						
Operating junction and storage ter	nperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS				MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	.,				
Forward voltage	V _F	I _F = 15 A	-	0.92	1.05	V				
		I _F = 15 A, T _J = 125 °C	-	0.78	0.85					
Reverse leakage current	I _R	$V_R = V_R$ rated	-	-	10					
neverse leakage current		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	5	300	μA				
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 \text{ A}, dI_F/dt = 50$	-	-	35					
Reverse recovery time	t _{rr}	$I_F = 1 A, dI_F/dt = 100$	-	-	30	no				
		T _J = 25 °C		-	26	-	ns			
		T _J = 125 °C	$I_F = 15 \text{ A}$	-	40	-				
Dook room ourrent	I _{RRM}	T _J = 25 °C	dl _F /dt = 200 A/μs V _B = 160 V	-	2.8	-	Α			
Peak recovery current		T _J = 125 °C	11	-	6.0	-				
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	37	-	nC			
		T _J = 125 °C	-	120	-	IIC				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS										
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction-to-case per diode	R _{thJC}	Mounting surface, flat, smooth and greased	-	-	1.1	°C/W				
Marking device		Case style TO-220AB 3L	30CTH02							

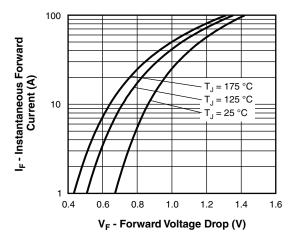


Fig. 1 - Typical Forward Voltage Drop Characteristics

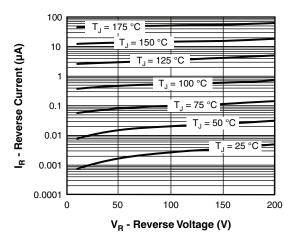


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

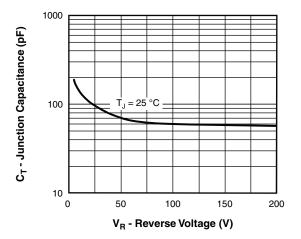


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

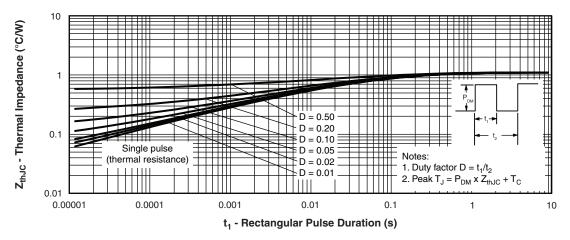
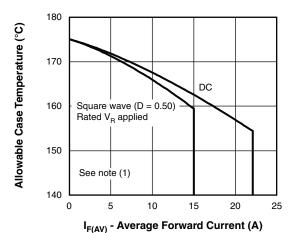


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

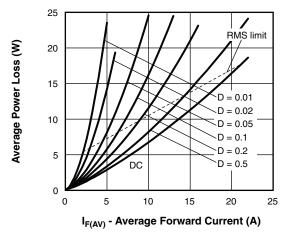


Fig. 6 - Forward Power Loss Characteristics

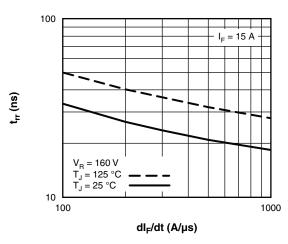


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

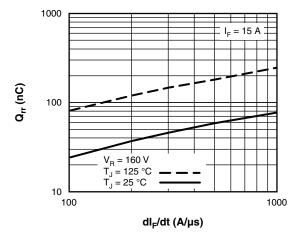
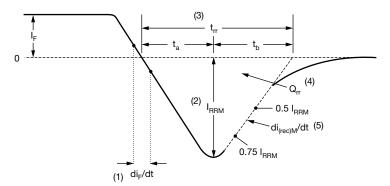


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

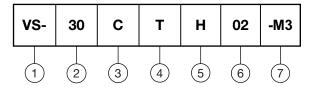
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (30 = 30 A)
- **3** C = common cathode
- **4** T = TO-220
- H = hyperfast recovery
- 6 Voltage rating (02 = 200 V)
- 7 Environmental digit:
 - -M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-30CTH02-M3	50	Antistatic plastic tubes							

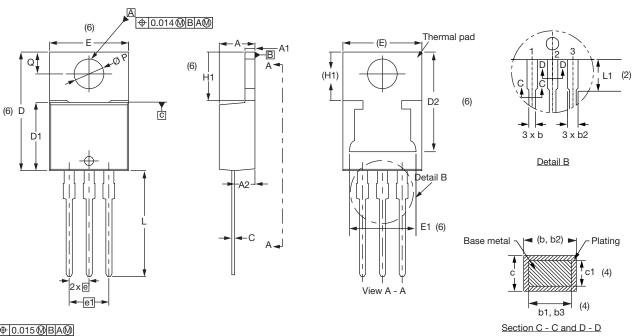
LINKS TO RELATED DOCUMENTS								
Dimensions <u>www.vishay.com/doc?96154</u>								
Part marking information	www.vishay.com/doc?95028							



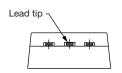
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3L TO-220AB

DIMENSIONS in millimeters and inches



⊕ 0.015 **M** B A **M**



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	.	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7	
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6	
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6	
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105		
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208		
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6	
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552		
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2	
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154		
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118		
D1	8.38	9.02	0.330	0.355		1		•			•		

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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